ABSTRACT

A semiconductor device includes a substrate including an active region, a first gate line and a second gate line in the active region, a first source/drain contact pattern in the active region at one side of the first gate line, a second source/drain contact pattern in the active region at one side of the second gate line, and a dummy source/drain contact pattern in the active region between the first gate line and the second gate line. The first gate line and the second gate line may be spaced apart from each other in the first direction and may extend in the second direction. The second direction may cross the first direction. A size of the dummy source/drain contact pattern may be less than a size of the first source/drain contact pattern and a size of the second source/drain contact pattern.

FIG. 1